WINSOURCE ELECTRONICS

THE DATASHEET OF

TS74230L

SPDT 30 W/60 W_{peak} Power Switch 1 MHz to 6.0 GHz

Features

- Frequency Range 1 MHz to 6.0 GHz
- Low insertion loss:
  0.20 dB @ 1.0 GHz
  0.30 dB @ 3.0 GHz
  0.65 dB @ 6.0 GHz
- High isolation:
  28 dB @ 3.0 GHz
  16 dB @ 6.0 GHz
- 30 W CW Power, 60 W_{peak} Peak Power
- Low power consumption, less than 1 mW
- No external DC blocking capacitors on RF lines
- All RF ports OFF state
- Versatile 2.6 V – 5.25 V power supply
- Charge pump disabled, −18 V supply needed
- Noise level better than −140 dBm kHz^{-1}

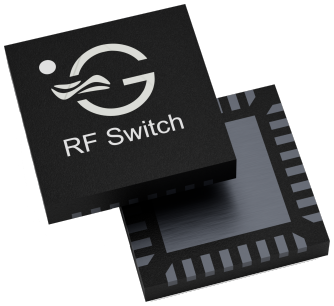


Figure 1: TS74230L in 4.0 x 4.0 mm^2 QFN 32-pin package.

Applications

- Private mobile and defense radios
- Public safety handsets
- Cellular infrastructure
- Satellite terminals
- Datalinks

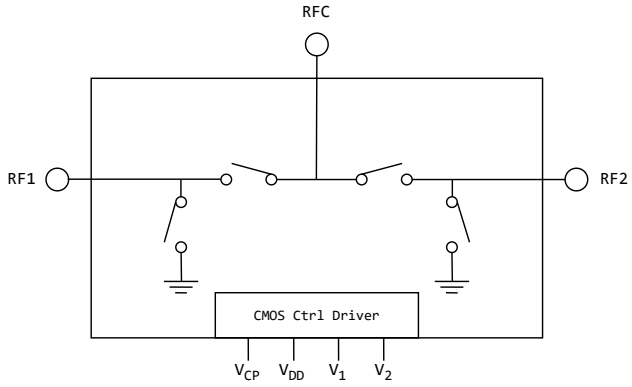


Figure 2: TS74230L functional diagram

General Description

The TS74230L is a 2nd Generation symmetrical reflective Single Pole Dual Throw (SPDT) switch designed for medium power switching applications. The TS74230L covers 1 MHz to 6.0 GHz bandwidth and provides low insertion loss, high isolation, and high linearity within a small package size. The TS74230L is a 30 W CW with peak power capability of 60 W, switch suitable for applications requiring low insertion loss, high isolation, and high linearity. TS74230L has charge pump disabled and requires an external -18 V supply, offering a noise level better than -140 dBm/1 kHz.

The TS74230L is packaged into a compact Quad Flat No lead (QFN) 4.0x4.0 mm^2 32 leads plastic package.

RoHS

RoHS10/REACH/Halogen free

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Ordering information

Table 1: Ordering Information

Device Part Number	Package Type	Notes
TS74230L	32 Pin 4.0x4.0x0.75 mm^3 QFN	Core part number
TS74230L-EVB	Evaluation Board	
TS74230LMTRPBF[1]	330 mm reel, 3 000 pcs	Full reel

[1] MTRPBF - M: Manufacturing, TR: Tape and Reel, and PBF: lead free.

Table 2: Tape and Reel Information

Form	Quantity	Reel Diameter	Reel Width
Tape and Reel	3 000	13” (330mm)	18mm

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Pin Assignment

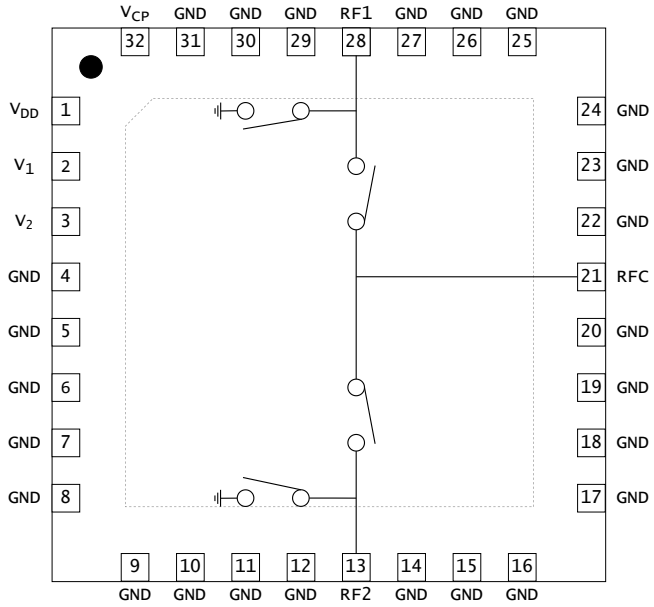


Figure 3: TS74230L pin assignment [top view]

Table 3: Pin Definition

Pin Number	Pin Name	Description
32	V_{CP}	Internal charge pump voltage output, connect a 1nF capacitor to GND on this node.
1	V_{DD}	DC Power Supply
2	V_1	Switch control input 1
3	V_2	Switch control input 2
13	RF2	RF port 2
21	RFC	RF Common port / Antenna port
28	RF1	RF port 1
4,5,6,7,8,9,10,11,12	GND	Connect to ground[2]
14,15,16,17,18,19,20		
22,23,24,25,26,27		
29,30,31		
33 [1]	GND	Ground thermal pad, please connect to GND

[1] The backside ground (thermal) pad of the package must be grounded directly to the ground plane of PCB with multiple vias, and adequate heat sinking must be used to ensure proper operation and thermal management.
[2] These pins are NC pins inside the package. To avoid floating pins around RF lines, we request these to be connected to ground.

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Absolute Maximum Ratings

Table 4: Absolute Maximum Ratings $T_A = +25$°C unless otherwise specified[1].

Parameter	Symbol	Value	Unit
Electrical Ratings			
Power Supply Voltage	V_{DD}	5.5	V
Storage Temperature Range	T_{st}	−55 – 125	°C
Operating Temperature Range	T_{op}	−40 – 85	°C
Maximum Junction Temperature	T_j	+140	°C
Maximum RF CW input power[3]	RFx/ANT	45.5	dBm
Maximum RF peak input power, 1% duty cycle, 10μs pulse [2]	RFx/ANT	49	dBm
Thermal Ratings			
Thermal Resistance (junction-to-case) – Bottom side	$R_{\theta jc}$	9.0	°C/W
Soldering Temperature	T_{solder}	+260	°C
ESD Ratings			
Human Body Model (HBM)	Level 1B	500 – $<$1000	V
Charged Device Model (CDM)	Level C3	$\geq$1000	V
Moisture Rating			
Moisture Sensitivity Level[4]	MSL	1	

[1] Maximum ratings are absolute ratings. Exposure to absolute maximum rating conditions for extended periods may affect device reliability and can cause permanent damage to the device. Exceeding one or a combination of the absolute maximum ratings may cause permanent and irreversible damage to the device and/or to surrounding circuit. Functional operation of the device is not implied in any conditions above those indicated in the Electrical Specifications section.
[2] Test frequency 800MHz.
[3] See Power De-rating table for low frequencies.
[4] Tagore recommends to store part in moisture barrier bags to preserve solderability.

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Electrical Specifications

Table 5: Electrical Specifications $T_A = +25°C; V_{DD} = +3.3V; 50\Omega$ Source/Load.

Parameter	Condition	Minimum	Typical	Maximum	Unit
Operating frequency	f	1		6000	MHz
Insertion loss	30 MHz		0.15		dB
unmatched, upto 4.5 GHz	1.0 GHz		0.18	0.30	dB
RFC – RFx	3.0 GHz		0.30		dB
	4.5 GHz		0.40		dB
Insertion loss[1]	30 MHz		0.15		dB
matched upto 6.0 GHz	1.0 GHz		0.20		dB
RFC – RFx	3.0 GHz		0.30		dB
	5.0 GHz		0.50		dB
	6.0 GHz		0.65		dB
Isolation	30 MHz		60		dB
unmatched, upto 4.5 GHz	1.0 GHz	40	43		dB
RFC – RFx	3.0 GHz		28		dB
	4.5 GHz		21		dB
Isolation[1]	30 MHz		60		dB
matched upto 6.0 GHz	1.0 GHz		43		dB
RFC – RFx	3.0 GHz		28		dB
	5.0 GHz		20		dB
	6.0 GHz		16		dB
Isolation[1]	30 MHz		60		dB
Isolation state	1.0 GHz		37		dB
RFC – RFx	3.0 GHz		24		dB
	5.0 GHz		16		dB

[1] Matched values are not guaranteed as they include performance of matching components. These components are beyond control of TagoreTech and therefore given values are indications, not guaranteed values.

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Table 6: Electrical Specifications $T_A = +25°C; V_{DD} = +3.3V; 50\Omega$ Source/Load.

Parameter	Condition	Minimum	Typical	Maximum	Unit
Operating frequency	f	1		6000	MHz
Return Loss	30 MHz		-30		dB
unmatched, upto 4.5 GHz	1.0 GHz		-30	-25	dB
$RFC - RFx$	3.0 GHz		-22		dB
	4.5 GHz		-20		dB
Return Loss[1]	30 MHz		-30		dB
matched upto 6.0 GHz	1.0 GHz		-30	-25	dB
$RFC - RFx$	3.0 GHz		-20		dB
	5.0 GHz		-22		dB
	6.0 GHz		-20		dB

[1] Matched values are not guaranteed as they include performance of matching components. These components are beyond control of TagoreTech and therefore given values are indications, not guaranteed values.

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Table 7: Electrical Specifications $T_A = +25°C; V_{DD} = +3.3V; 50\Omega$ Source/Load.

Parameter	Condition	Minimum	Typical	Maximum	Unit
Operating frequency	f	1		6000	MHz
Harmonic Distortion					
H_2	800MHz, P_{in} =40dBm		-92		dBc
H_3	800MHz, P_{in} =40dBm		-95		dBc
IIP3	800MHz		77		dBm
Power and Compression point					
P_{maxCW}[2]	Max RF CW Power		43		dBm
$P_{maxpeak}$	Max RF Peak Power		48		dBm
$P_{maxhot\ RFx}$[5]	Max RF CW Power, hot switching		37		dBm
$P_{maxhot\ RFC}$[5]	Max RF CW Power, hot switching		37		dBm
$P_{0.1dB}$	800MHz, CW		45		dBm
P_{1dB}[1]	800MHz, CW		48		dBm
$P_{peak0.1dB}$	800MHz, 1% duty cycle, 10μs pulse		48		dBm
Noise					
CP switching noise[4]	RBW=1kHz		-140		dBm
Switching Time					
t_{ON}[9]	Switch ON time		900	1170	ns
t_{OFF}[9]	Switch OFF time		900	1170	ns
t_{RISE}[9]	Switch RISE time		500	600	ns
t_{FALL}[9]	Switch FALL time		500	600	ns
t_{wON}	Minimum Switch ON time		3.6		μs
t_{wOFF}	Minimum Switch OFF time		3.6		μs
$f_{PRR}, V_{CPext} = -18$ V[6]	Maximum pulse repetition rate		>20		kHz
$t_{startup}, C_{VCP}$ = ext $= -18$ V[6]	startup time		40		ms
Power Supply, DC					
Power Supply[7]	V_{CP}	-19	-18	-17	V
Power Supply	I_{CP}	100			μA
Control voltage[8]	Power Supply V_{DD}	2.6	3.3	5.25	V
	All control pins high, V_{ih}	1.0	3.3	5.25	V
	All control pins low, V_{il}	-0.3	0	0.5	V
Control current	All control pins high, I_{ih}			7.5	μA
	All control pins low, I_{il}		0		μA
Current consumption	I_{DD}, active mode (V_{DD} on)		160	260	μA

[1] $P_{1\,dB}$ has been given for comparison reasons only. Please do not exceed Absolute Maximum ratings.
[2] See Power De-rating table
[5] Dependent on thermal design and surrounding circuits.
[6] External -18 V applied to V_{CP} pin. TS74230L has internal chargepump disabled and therefore requires external -18 V voltage.
[7] V_{DD} should be applied first before V_{CP}. Minimum time between V_{DD} and V_{CP} should be 50 μs.
[8] Control voltage V_{ih} cannot be higher than V_{DD} (to avoid forward biasing of ESD diode)
[9] Switching time characterization done at 30 Hz and 500 Hz pulse repetition rate (rate to change switch state, for example between RFC-RF1 and RFC-RF2).

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Switching time definition

Example of the definition by using 10 W/40 dBm signal. We apply 10W signal to RF port, stabilized with isolator. Isolator is needed as our switch shows to RF port approximately 4Ω impedance. Lets assume that that switch insertion loss is 0.3 dB. Therefore 90% of the RF signal is 39.55 dBm and 10% of the RF signal is 1W/30dBm. We need to take into account 0.3dB insertion loss, therefore numbers are 39.25 dBm and 29.7 dBm respectively. We change the control from low to high and our time reference point is when our control signal exceeds lower threshold value $\mathrm{V_{ihlow}}$. In certain measurements when control signal rise time is significantly shorter than RF output signal, we approximate start of the clock with 50% point of control signal.

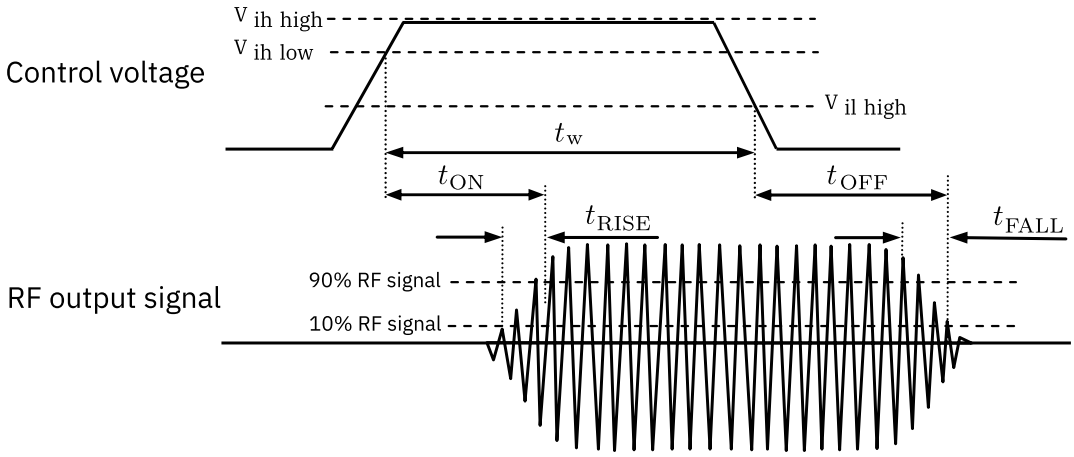


Figure 4: Switching time definition, t_{ON}, t_{OFF}, t_{RISE}, t_{FALL}. Minimum pulse width t_{w}.

Our component uses integrated charge pump. Maximum pulse repetition rate defines what is maximum frequency for switching events. Please do not exceed given maximum frequency. By feeding external -18 V to $\mathrm{V_{CP}}$, one can improve maximum pulse repetition rate f_{PRR}. Feeding external -18V to $\mathrm{V_{CP}}$, one can drive switch at least to 20kHz f_{PRR}. Expect current consumption of 10mA of -18V.

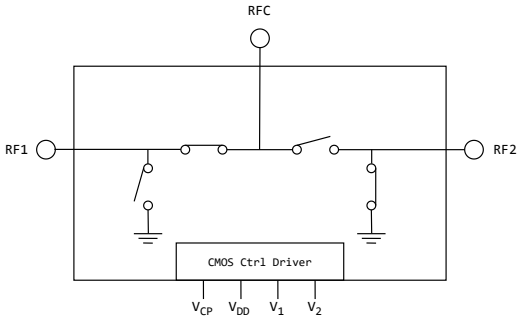
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Switch Control table

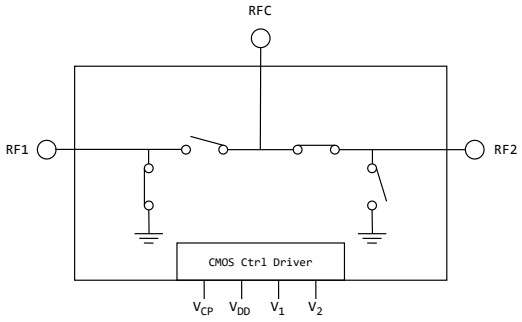
Table 8: Switch Control Table

V_{DD}[1]	V_2	V_1	**Switch state**
1	0	0	$RFC - RF1$ ON[2]
1	0	1	$RFC - RF2$ ON
1	1	0	ISO (Isolation), RFC port open, RF ports shorted[3].
0	0	0	V_{DD} off (Isolation), all FETs are on, short shown to RFC and RF ports

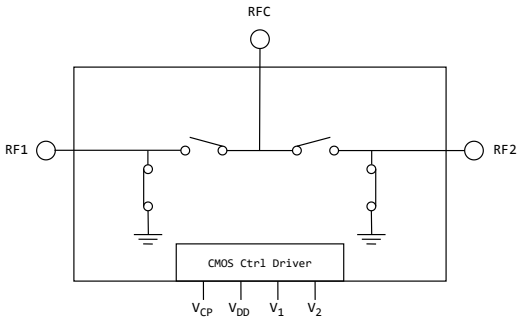
[1] V_{DD} should be applied first before V_1 and V_2, otherwise may cause damage to the device.
[2] There are internal pull-downs to ground on both V_1 and V_2 control pins, the state at start-up without any control voltage applied will be $RFC - RF1$ ON.
[3] If ISO state is not used, the switch can be operated with single control pin V_1
[4] V_{DD} should be applied first before V_{CP}. Minimum time between V_{DD} and V_{CP} should be 50 μs.



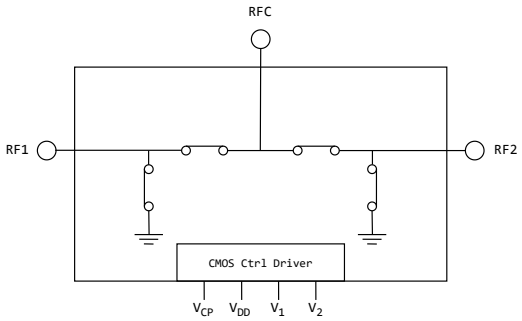
RFC-RF1 ON



RFC-RF2 ON



ISO (Isolation state)



V_{DD} off state

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Theory of Operation

Isolation modes

TS74230L has two isolation modes. Both Isolation mode measurements are shown at electrical performance section. Both modes described below.

Device powered off

When V_{DD} is 0 V, all switch RF transistors are on, ie. every MOSFET is on. This means that series MOSFETs and shunt MOSFETs are conducting. Every RF port is essentially connected to ground, including RFC port. This is practical when device is directly connected to RFC, there is certain protection against induced electrical fields. This can partially protect radio equipment against electrical fields, when device is not in usage.

Device powered, ISO state

In this state, series MOSFETs are OFF, ie. OPEN and shunt MOSFETs are on, ie. closed. RF1 to RF2 isolation is maximum and antenna is completely isolated. RFC port is open, whereas RFx ports are showing effectively short. Low frequency isolation in this case is approximately 60 dB as basically there is DC block due to open FETs.

Applications

TS74230L is offering 30 W/60 W_{peak} capability from 1 MHz to 6000 MHz frequency band. Applications include narrowband and multi-octave wideband radios, jammers, EMC testing, public mobile radios, industrial and scientific applications. In the past, such applications were covered with power hungry and complex PIN diodes, TS74230L significantly reduces design complexity for such RF switching needs. TS74230L works well upto 5 GHz frequency without external matching components, for frequency above 4.5 GHz, matching is recommended. Datasheet provides an example matching and its performance.

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Schematics and Evaluation Board

S-parameters of the both presented EVBs can be downloaded from link: Download TS74230L S-parameters

Table 9: Port definitions in s-parameter files and plots.

PIN name	Port numbers	S-parameters	Function
RFC	1	S11	
RF1	2	S22	
RF2	3	S33	
RF1ON	12	S21	RFC-RF1 ON
RF2ON	13	S31	RFC-RF2 ON

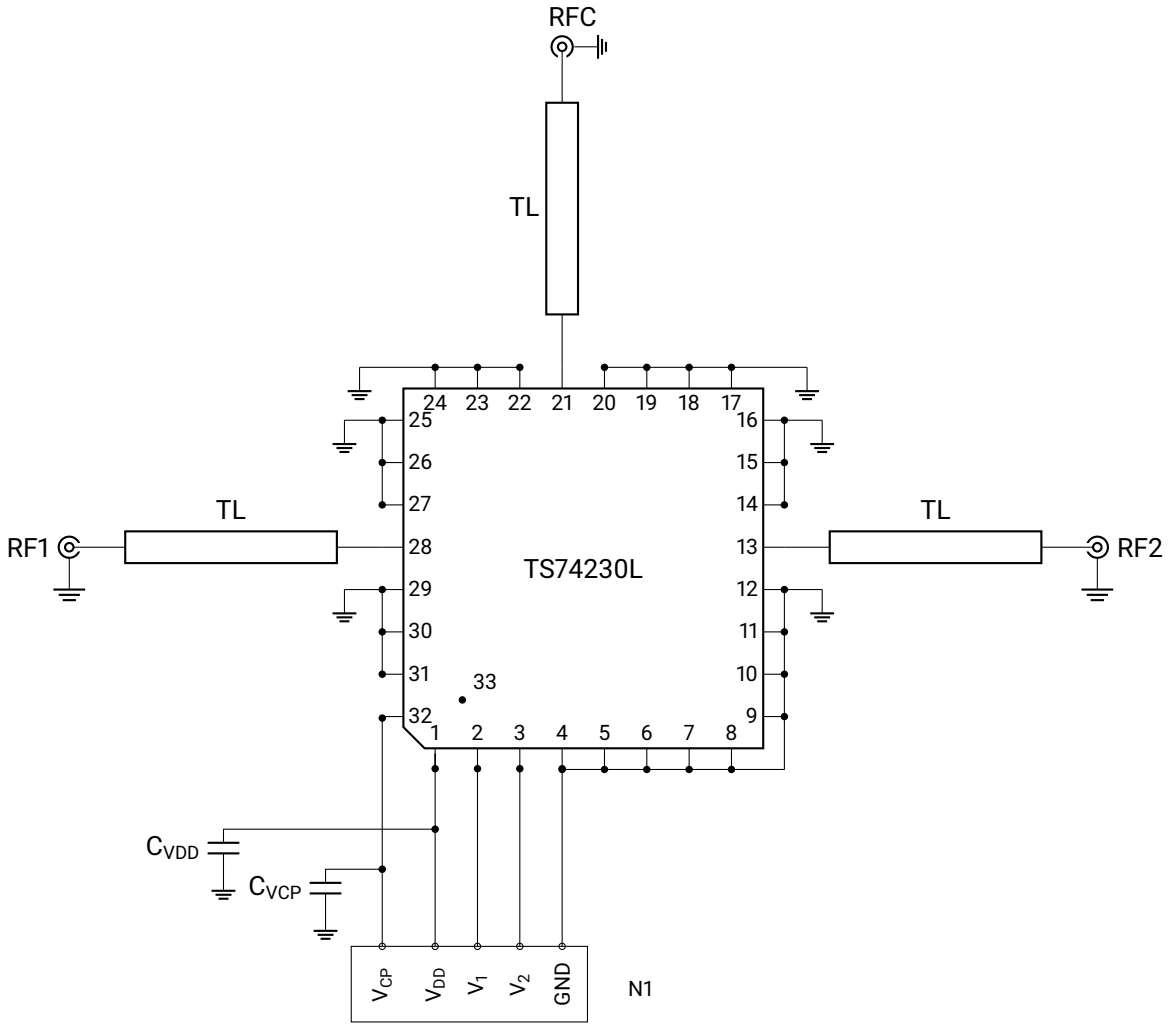
Content of s-parameter repository:

```
TS74230L.zip
├── IDX_00_no_match ..... Directory for s-parameters without matching components
│   ├── Readme.txt
│   ├── TS74230L_RFOFF_3PORT.s3p ..... S3P file for ISO mode
│   ├── TS74230L_VDDOFF_3PORT.s3p ..... S3P file for VDD off mode
│   ├── TS74230L_RF1ON_3PORT.s3p ..... S3P file for RFC-RF1ON mode
│   └── TS74230L_RF2ON_3PORT.s3p ..... S3P file for RFC-RF2ON mode
└── IDX_01_wideband ..... Directory for s-parameters with matching components, 6.0 GHz
    ├── Readme.txt
    ├── TS74230L_RFOFF_3PORT.s3p ..... S3P file for ISO mode
    ├── TS74230L_VDDOFF_3PORT.s3p ..... S3P file for VDD off mode
    ├── TS74230L_RF1ON_3PORT.s3p ..... S3P file for RFC-RF1ON mode
    └── TS74230L_RF2ON_3PORT.s3p ..... S3P file for RFC-RF2ON mode
```


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Performance upto 4.5 GHz, unmatched

TS74230L shows best performance upto 4.5 GHz frequency without any matching components. Only two external components are recommended, 1 nF for V_{CP} and 10nF forV_{DD} lines for supporting charge pump and power supply.



Schematics of TS7423L EVB

Table 10: Components used for TS74230L EVB

Reference	Part number / Value	Description	Notes
C_{VDD}	10 nF	Capacitor	
C_{VCP}	1 nF	Capacitor	

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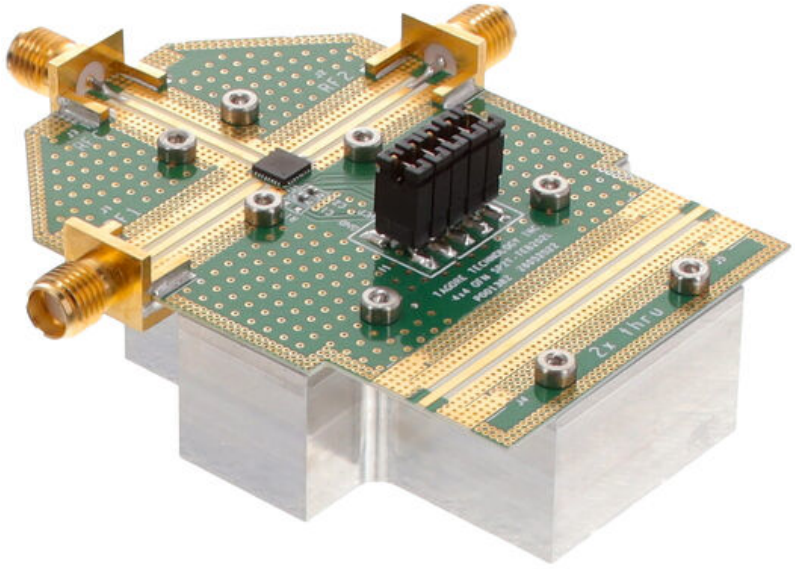


Photo of TS74230L EVB

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Performance upto 6.0 GHz, matched

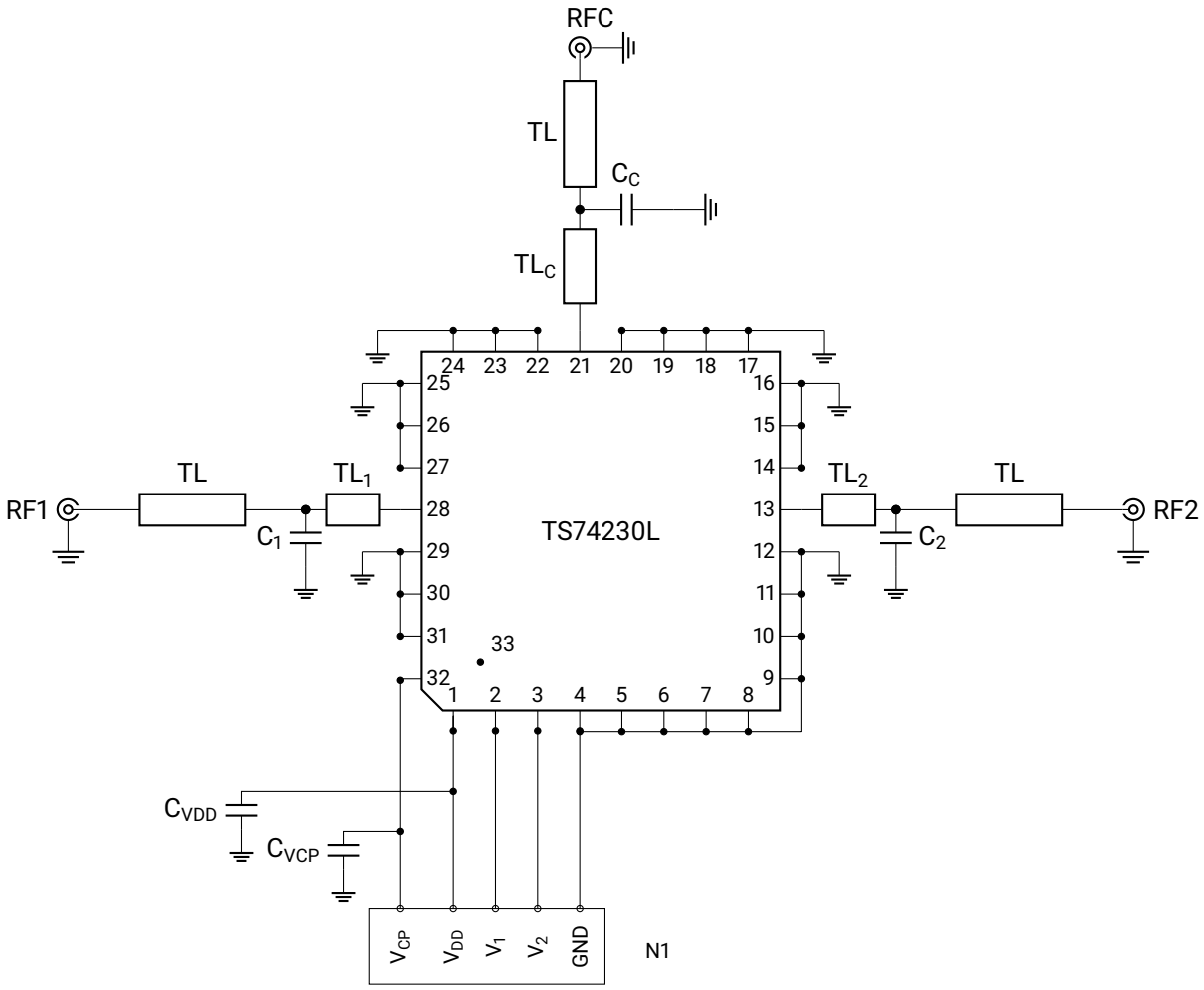


Table 11: Matching components used for 6.0 GHz matching

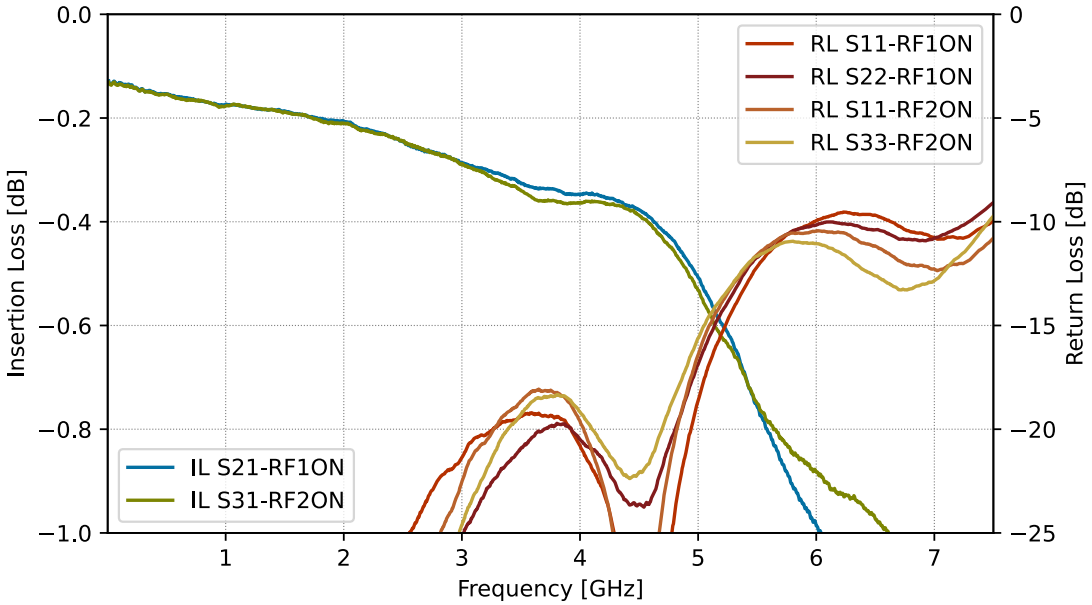
Reference	Part number / Value	Description	Notes
TL_C	1.8 mm	CPW length	Edge of SW to edge of capacitor
C_C	0603N0R2BW251	Ceramic capacitor	0.2 pF, 250 V, ± 0.1 pF
TL_1	0.4 mm	CPW length	Edge of SW to edge of capacitor
C_1	0603N0R2BW251	Ceramic capacitor	0.2 pF, 250 V, ± 0.1 pF
TL_2	0.4 mm	CPW length	Edge of SW to edge of capacitor
C_2	0603N0R2BW251	Ceramic capacitor	0.2 pF, 250 V, ± 0.1 pF
C_{VDD}	10 nF	Capacitor	
C_{VCP}	1 nF	Capacitor	

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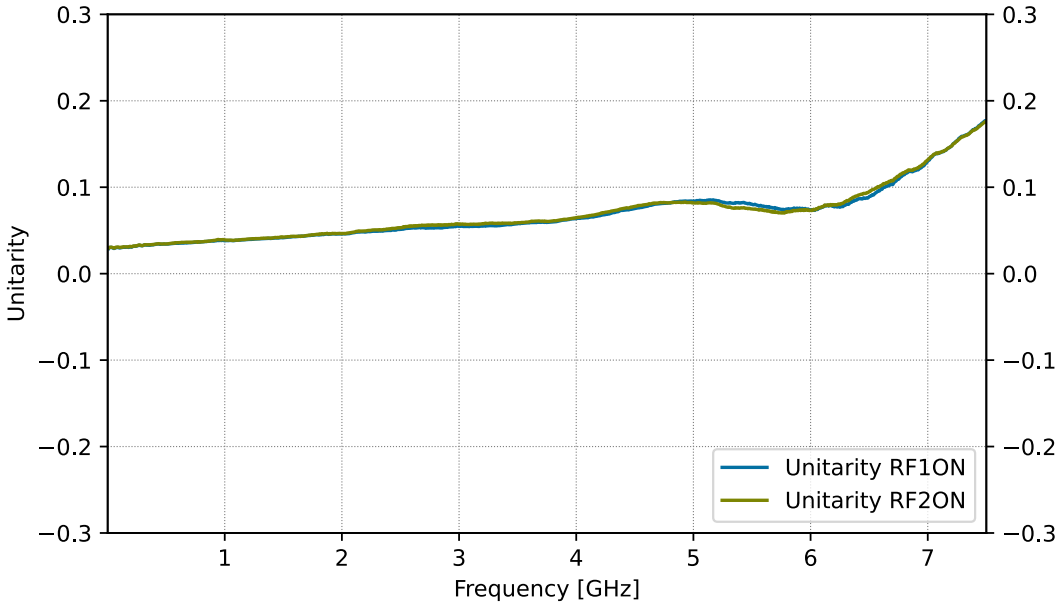
Typical characteristics

Performance upto 4.5 GHz, unmatched

These measurements have been taken from TS74230L EVK, CPW losses have been de-embedded from the measurements. Device does not require any matching components for operation upto 4.5 GHz. Going above 4.5 GHz, performance can be improved by adding matching to ports. Our matching example shows excellent performance upto 6.0 GHz.

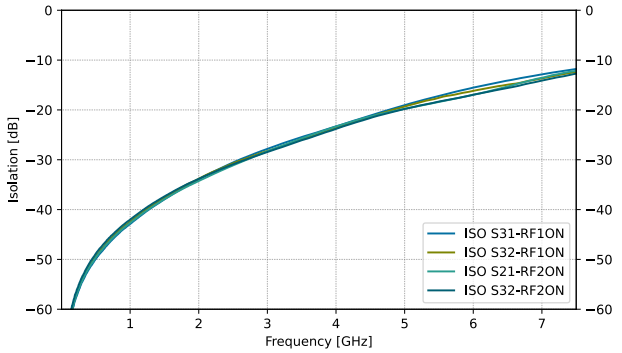


Insertion loss and Return loss, $\mathrm{RFC} - \mathrm{RFx}$.

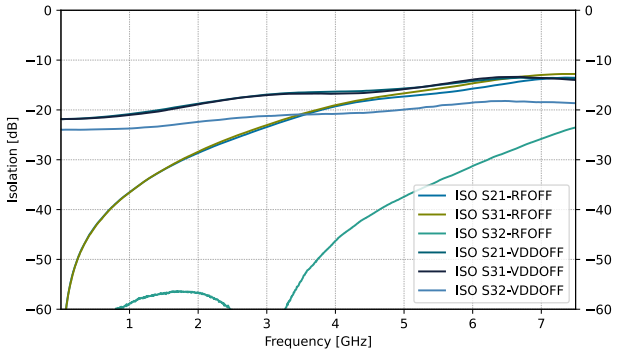


Power absorption of the switch $1 - |S_{11}|^2 - |S_{21}|^2 - |S_{31}|^2$, $\mathrm{RFC} - \mathrm{RFx}$.

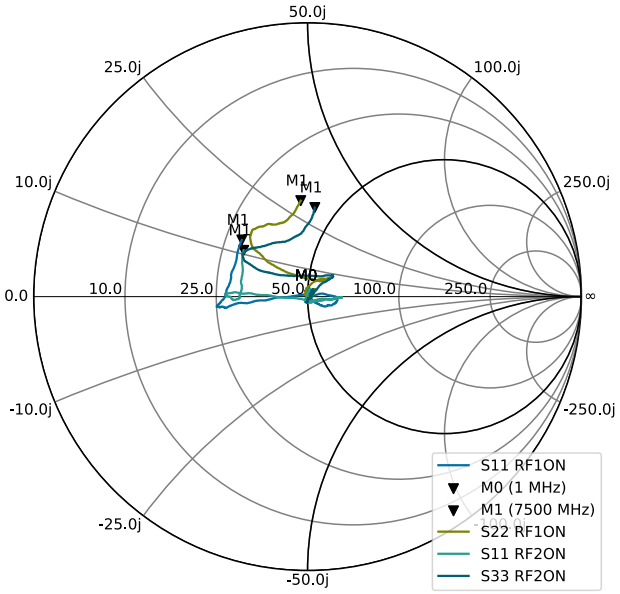
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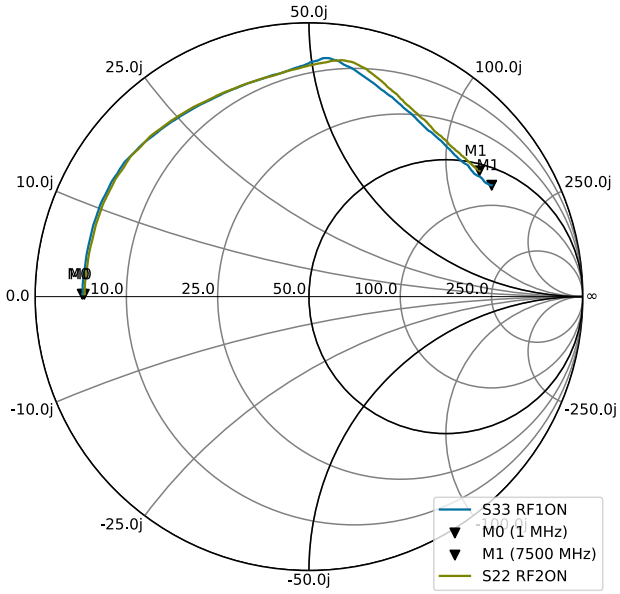
Isolation between RFC to non-active RFx and active RFx to non-active RFx.



RFC – RFx isolation and RFx – RFx isolation at ISO mode and V_{DD} off (Isolation).



RFC and RFx matching at ON state.

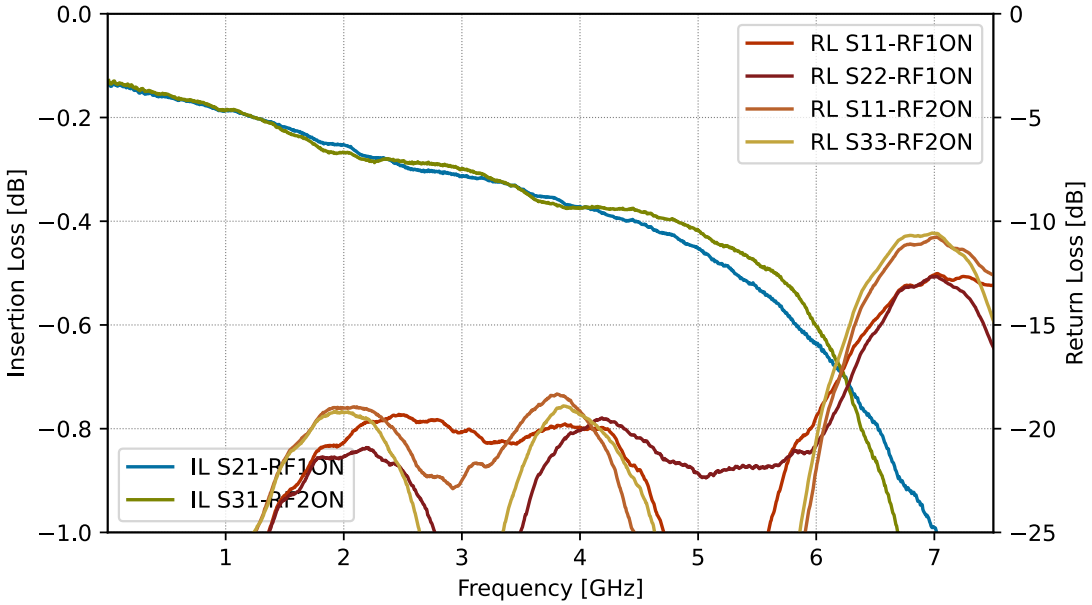


Non-active RFx port impedance. Low frequency starts from closed and circulates towards open at higher frequencies.

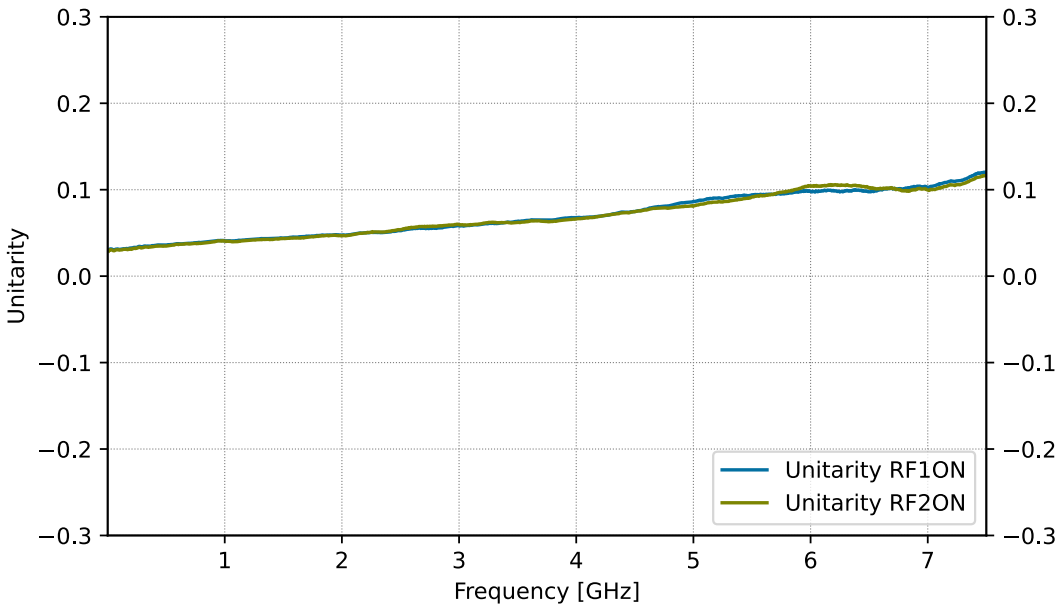
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Performance upto 6.0 GHz, matching applied to EVK

These measurements have been taken from TS74230L EVK, matching components applied. CPW losses have been de-embedded from the measurements, but matching component losses are present.

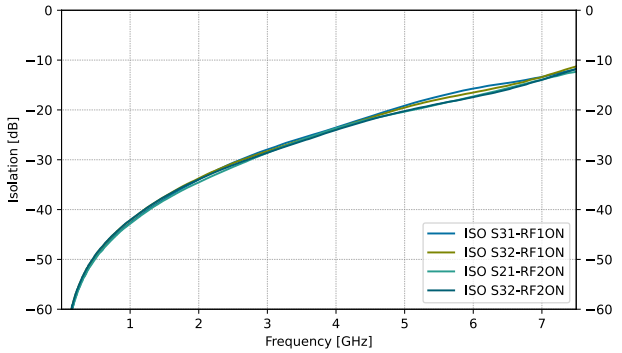


Insertion loss and Return loss, $\mathrm{RFC} - \mathrm{RFx}$.

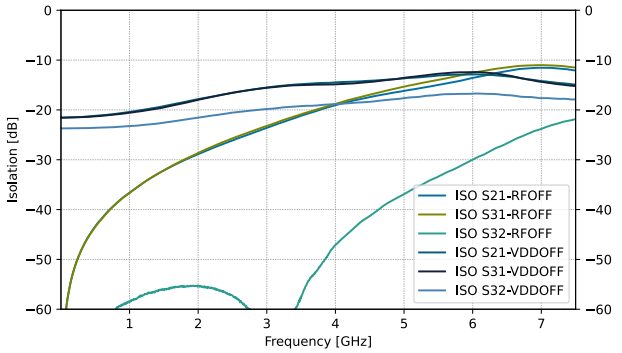


Power absorption of the switch $1 - |S_{11}|^2 - |S_{21}|^2 - |S_{31}|^2$, $\mathrm{ANT} - \mathrm{RFx}$.

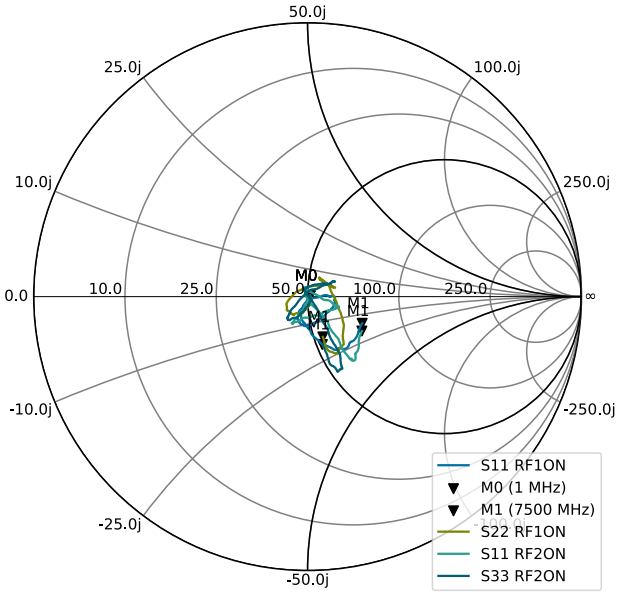
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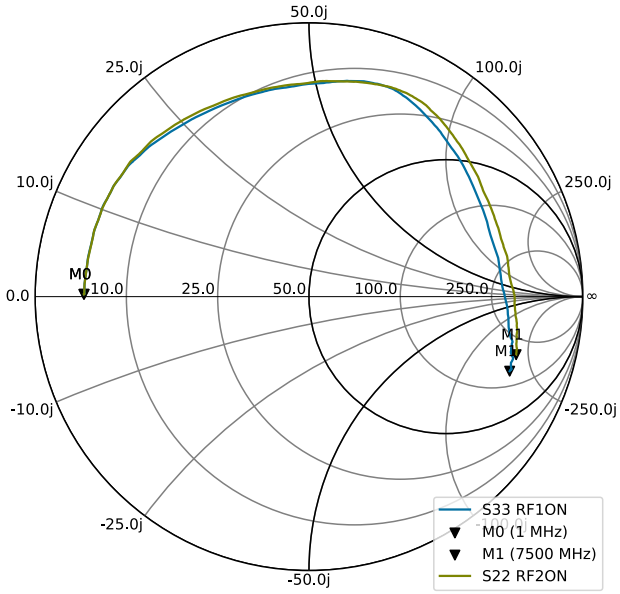
Isolation between RFC to non-active RFx and active RFx to non-active RFx.



RFC – RFx isolation and RFx – RFx isolation at ISO mode and V_{DD} off (Isolation).



RFC and RFx matching at ON state.

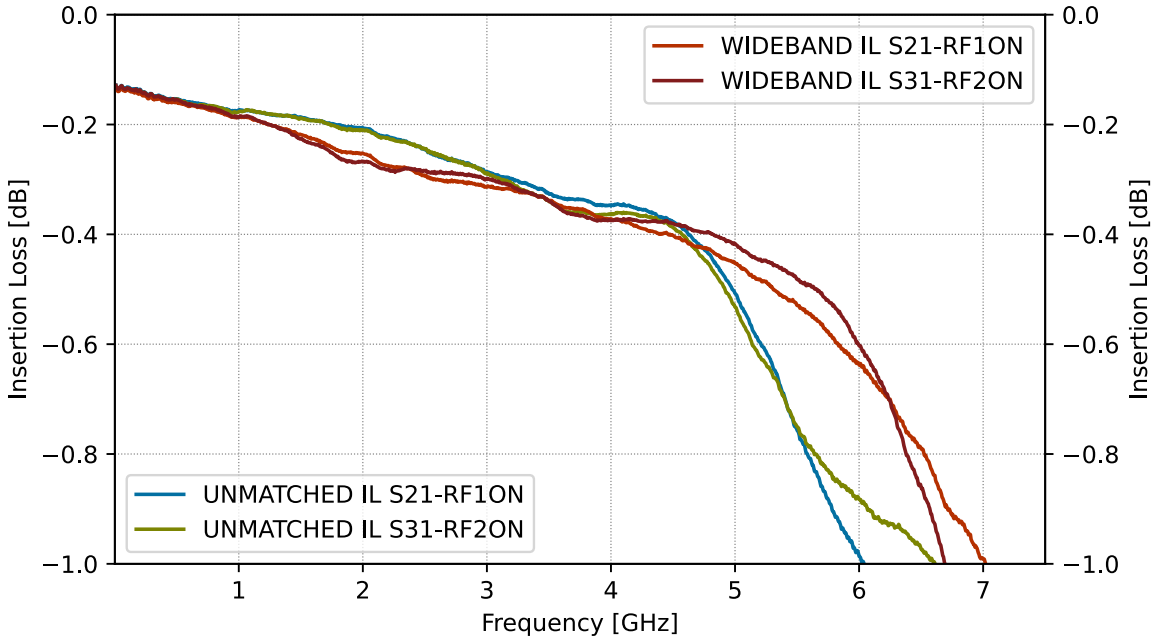


Non-active RFx port impedance. Low frequency starts from closed and circulates towards open at higher frequencies.

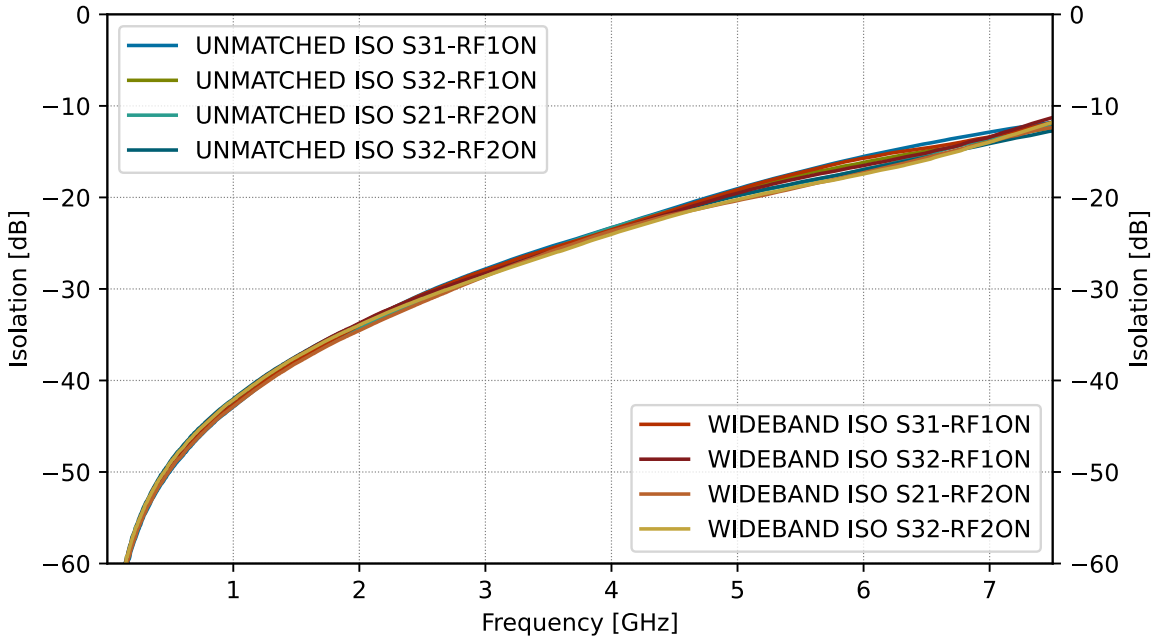
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Comparison plots of matched and unmatched switch.

Below Insertion Loss and Isolation comparison plots of matched and unmatched switch. Matching extends frequency response to 6.0 GHz without affecting isolation.



Insertion loss comparison of matched to 6.0 GHz and unmatched switch.



Isolation comparison of matched to 6.0 GHz and unmatched switch.

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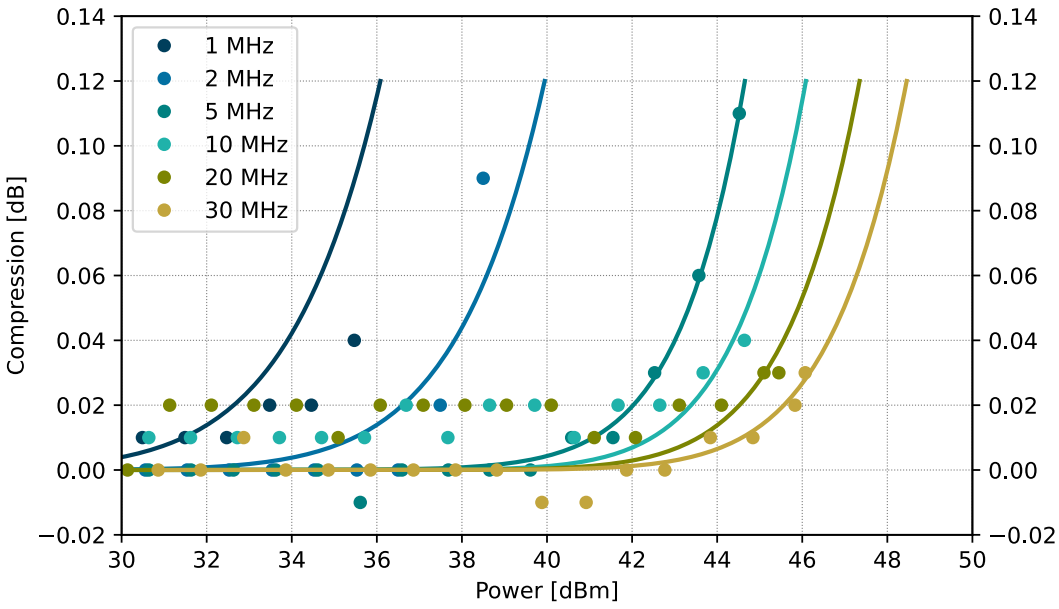
Power De-rating

TS74230L has power handling de-rating below 30MHz. Power de-rating table has been defined for 50ohm environment.

Table 12: Power De-Rating table

Start f	**Stop** f	**Max Power**	**Unit**
1 MHz	2 MHz	34	dBm
2 MHz	5 MHz	36	dBm
5 MHz	10 MHz	42	dBm
10 MHz	20 MHz	44	dBm
20 MHz	$f_{\max}$	45	dBm

TS74230L Continuous Wave (CW) compression measurement are presented. Measurements are conducted in room temperature $T_A = +25$°C. Values of De-Rating table takes into account manufacturing tolerances and margins. Measurements are presented as dot (•) and model and extrapolations presented as line (–).



TS74230L CW Compression measurement in room temperature $T_A = +25$°C.

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Device Package information

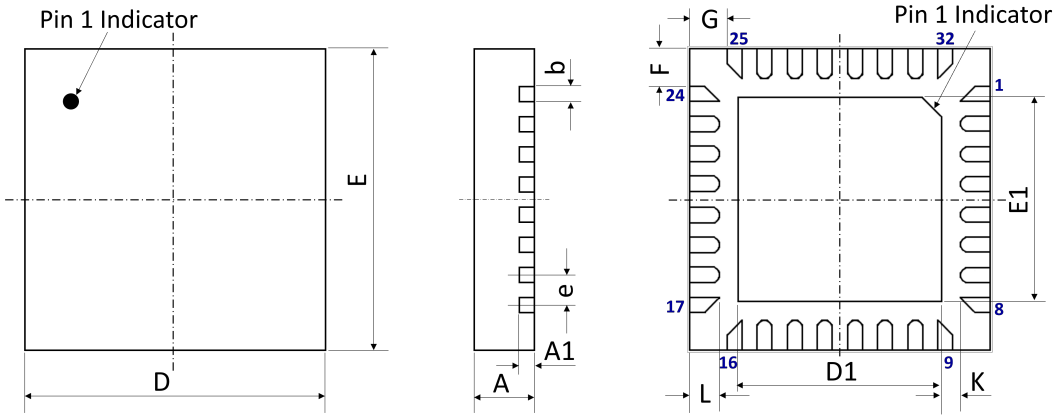


Figure 8: 32-pin QFN 4.0 x 4.0 x 0.75 mm^3 package drawing.

Please refer to application notes TN-001 and TN-002 at TagoreTech web page for PCB and soldering guidelines.

Table 13: Device Package Dimensions

Dimension	Value [mm]	Tolerance [mm]	Dimension	Value [mm]	Tolerance [mm]
A	0.75	±0.05	E	4.00 BSC	±0.05
A1	0.203	±0.02	E1	2.70	±0.05
b	0.20	+0.05/-0.07	F	0.50	±0.05
D	4.00 BSC	±0.05	G	0.50	±0.05
D1	2.70	±0.05	L	0.40	±0.05
e	0.40 BSC	±0.05	K	0.25	±0.05

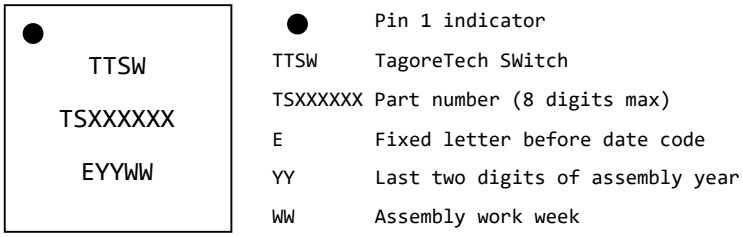


Figure 9: Part marking specification.

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PCB Land Design

Notes:

- 4-layer PCB is recommended.
- Via diameter is recommended to be 0.3mm to prevent solder wicking inside the vias.
- Thermal vias shall only be placed on the center pad.
- The maximum via number for the center pad is 11(X)×11(Y)=121.

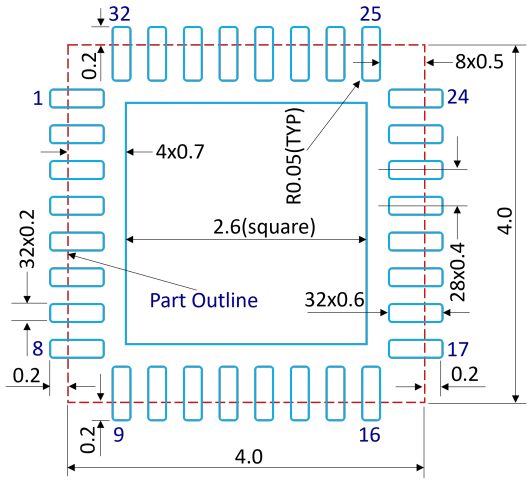


Figure 10: PCB land pattern, dimensions in [mm].

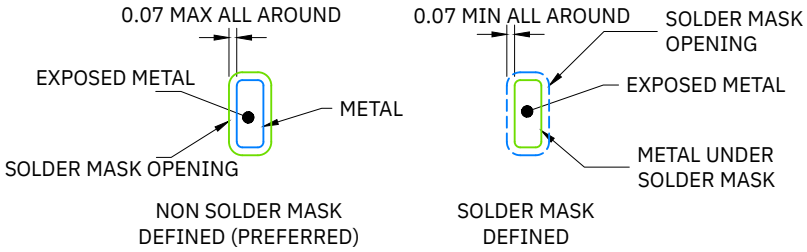


Figure 11: Solder mask opening, dimensions in [mm].

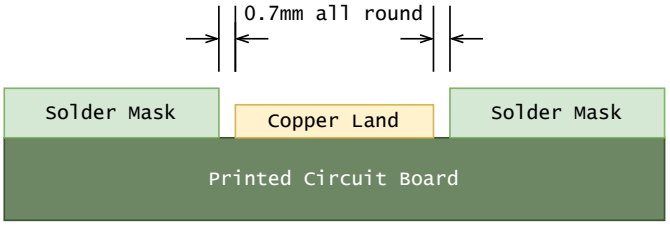


Figure 12: Preferred solder mask opening, side view, dimensions in [mm].

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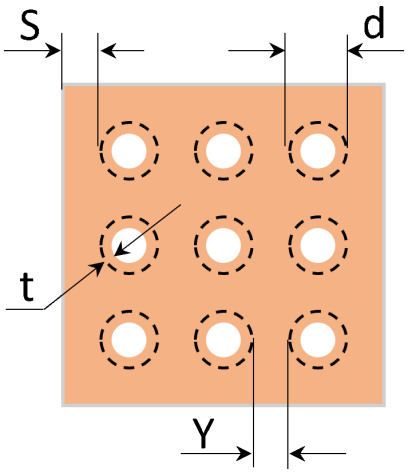


Figure 13: Thermal Via Pattern, Recommended Values: S≥0.15 mm; Y≥0.20 mm; d=0.2 mm; Plating Thickness t=25μm or 50μm.

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PCB Stencil Design

Notes:

- Laser-cut, stainless steel stencil is recommended with electro-polished trapezoidal walls to improve the paste release.
- Stencil thickness is recommended to be 125 μm.

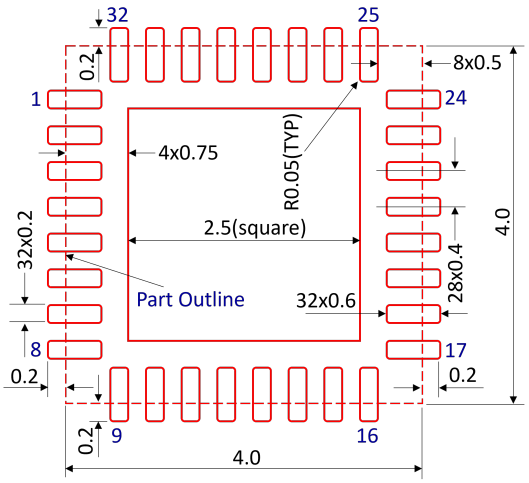


Figure 14: Stencil Openings, dimensions in [mm].

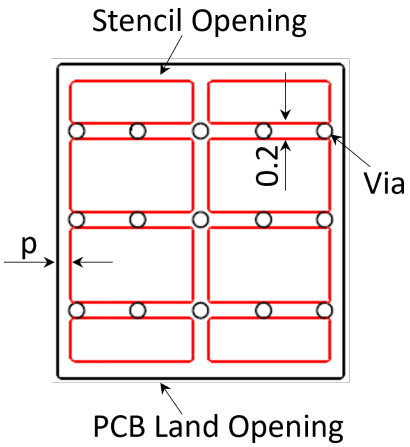
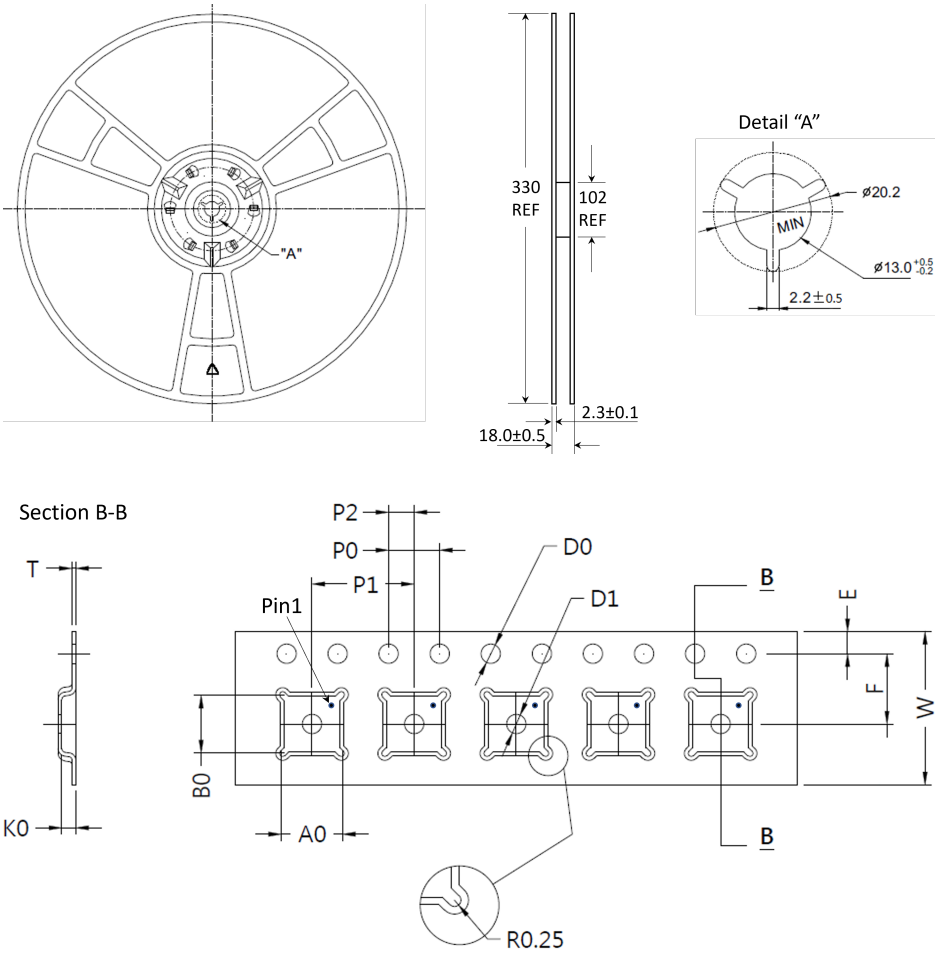


Figure 15: Stencil Openings Shall not Cover Via Areas If Possible, dimensions in [mm].

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Tape and Reel Information



A0[mm]	B0[mm]	D0[mm]	D1[mm]	E[mm]	F[mm]	K0[mm]	P0[mm]	P1[mm]	P2[mm]	T[mm]	W[mm]
4.35	4.35	1.50	1.50	1.75	5.50	1.10	4.00	8.00	2.00	0.30	12.00

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Glossary

IL	Insertion loss
ISO	Isolation
RL	Return loss
VSWR	Voltage Standing Wave Ratio
RFC	RF Common port, sometimes referred as ANT
RFx	RF Port number x
Unitarity	Describes power absorption of the component, $1 - \|S_{11}\|^2 - \|S_{21}\|^2 - \|S_{31}\|^2$

Changelog

Table 14: Changelog

Date	Revision	Notes
10/10/2025	5.0	New release with updated information, frequency range extended from 1 MHz to 6.0 GHz
01/12/2026	5.01	Low frequency compression measurement added
01/29/2026	5.02	Sequence guidance added : Minimum time between V_{DD} and V_{CP} should be 50 μs.
06/26/2026	5.04	Switching time characterisation added, table of content added and a few typos corrected.

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